Norstel's commercial product range includes 50.8mm, 76.2mm and 100mm diameter 4H Semi-Insulating Silicon Carbide (SiC) substrates that are available in on-axis as well as custom defined off-axis orientation. Norstel's unique and patented HTCVD crystal growth technology is the key enabler to purer products combining high and uniform resistivity with a very low defect density.

STANDARD SPECIFICATION FOR 3" DIAMETER ON-AXIS SEMI-INSULATING SiC SUBSTRATES:

- Diameter: 76.2 ± 0.4 mm
- Polytype: 4H
- Orientation (center point): (0001) ±0.25 deg
- Type: Semi-insulating (HTCVD high purity)
- Resistivity: ≥ 1E7 Ohm-cm
- Thickness: 350 ± 25 µm
- TTV: ≤ 5 µm
- LTV: ≤ 2 µm
- Warp: ≤ 40 µm
- MPD (3mm edge exclusion): ≤ 10 cm²
- Surface finish (Si-face): Epi-ready (CMP) Rq ≤ 0.2 nm
- Surface finish (C-face): Optical Rq ≤ 3.0 nm

Ref: 251-B-Q January 2017

For more information please contact Norstel sales!
email: sales@norstel.com